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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

ATTORNEY DOCKET MIT8288CON

Kim et al.  
APPLICANT

Herewith  
FILING DATE

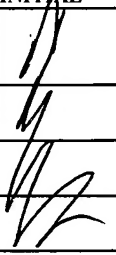
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10/023047  
12/13/01



**U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	AA	6,064,076	5/16/00	Chen et al.			5/20/98
	AB	4,378,259	03/29/83	Hasegawa et al.			12/24/80
	AC	4,680,602	July, 1987	Watanabe et al.	357	17	
	AD	4,218,270	July, 1987	Hasegawa et al.			
	AE						
	AF						
	AG						
	AH						

**FOREIGN PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
	AI	19756856	7/2/98	Germany			No
	AJ	54-146984	11/1979	Japan			
	AK	06*-061,525	11/1979	Japan			
	AL						
	AM						

**OTHER DOCUMENTS** (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL		
	AN	Chin, T.P., J.C.P. Chang, K.L. Kavanagh and C.W. Tu, "Gas-source molecular beam epitaxial growth, characterization, and light-emitting diode application of $\text{In}_x\text{Ga}_{1-x}\text{P}$ on GaP(100)," <u>Applied Physics Letters</u> , vol. 62, no. 19, May 10, 1993, pp. 2369-2371.
	AO	Kim, A.Y. and E.A. Fitzgerald, "Engineering Dislocation Dynamics in $\text{In}_x(\text{Al}_y\text{Ga}_{1-y})_{1-x}\text{P}$ Graded Buffers on GaP by MOVPE," presented at the Defect and Impurity Engineered Semiconductors II Symposium, San Francisco, California, April 13-17, 1998, published in Materials Research Society Symposium Procedures, vol. 510, pp. 131-135.

EXAMINER 

DATE CONSIDERED 9/28/00

**EXAMINER:**

Initial if citation considered, with the reference citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.